

# RENESAS TECHNICAL UPDATE

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Renesas Electronics Corporation

Product Category	EEPROM		Document No.	TN-LME-A004A/E	Rev.	1.00
Title	Site change of Assembly / Final Test for Renesas parallel EEPROM products.(3)		Information Category	Change or addition of Production Line		
Applicable Product	Parallel EEPROM HN58C1001 series, HN58V1001 series HN58C256A series, HN58V256A series HN58C257A series, HN58V257A series HN58V65A series, HN58V66A series	Lot No.	Reference Document	TN-LME-B004A/E TN-LME-A003A/E		
		After April 2013				

## 1. Summary

Assembly / Final test site of parallel EEPROM will change from "Renesas High Components,Inc.(RHC)" to "MTEX Matsumura CORPORATION (MTEX)", "MTEX VIETNAM CO.,LTD(MVC)" for higher production flexibility and keep stability long term support.

We have corrections for package inner-wire diameter and sample schedule about the technical update(TN-LME-A003A/E) issued on July12/2012.

We would appreciate your cooperation to recognition of this notification.

## 2. Corresponding products

All packaged Parallel EEPROM products,

1Mbits: HN58C1001 series, HN58V1001 series

256Kbits: HN58C256A series, HN58V256A series, HN58C257A series, HN58V257A series

64Kbits: HN58V65A series, HN58V66A series

Note. The Pb plating EEPROM products already finished production .So we will change only Pb-free products.

## 3. Reason of change

We will aim at higher production flexibility and keep stability long term support.

## 4. Schedule(correction item from TN-LME-A003A/E)

1	Please inform us the necessity of the evaluation samples.	November 2012
2	Start to supply the evaluation samples.	November 2012
3	Start to supply the reliability report at (MTEX)(MVC) and environment data.	November 2012
4	Start mass production at New site (MTEX),(MVC).	April 2013

Note. The products in (RHC) are limited to stock.

## 5. DC/AC characteristics, Package outline, Package mounted condition and quality control

The Products in (MTEX)and (MVC) are equal to them in (RHC) on DC/AC characteristics, Package outline, Package mounted condition and quality control.

6. Assembly / Final test Sites

Sites for each process are shown below.

Process	Site
Dicing — Die bonding — Wire bonding — Molding	MVC
Plating — Cutting ,Lead forming — Burn In — Marking — Electrical characteristics test — Final visual inspection — Packing	MTEX

7. Specification changes

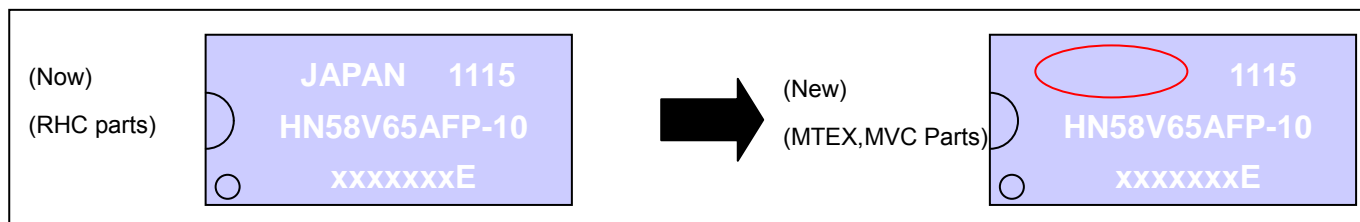
1) Package inner wire diameter(correction item from TN-LME-A003A/E)

Package	Now(Site : RHC)	New(Site : MVC/MTEX)
TSOP-28pin, TSOP-32pin	25um φ	23um φ
SOP-28pin, SOP-32pin	27um φ	25um φ
DILP-28pin	27um φ	25um φ

The electrical characteristics and reliability do not change, even though inner wire diameter change

2) Marking specification

Country of origin marking will be deleted. Please refer to below picture.



3) Laser marking for DILP28

Marking method will change from ink-marking to laser-marking for HN58C256AP series, HN58V256AP series, HN58V65A series and HN58V66A series.

8. List of part number

Renesas part number	Ordering part number	Memory density	Package	Innerwire diameter	Detasheet Document number
HN58C1001FPxx	HN58C1001RFPxx	1Mbits	SOP-32pin	25umφ	RJJ03C0129
HN58C1001Txx	HN58C1001RTxx	1Mbits	TSOP-32pin	23umφ	RJJ03C0129
HN58V1001FPxx	HN58V1001RFPxx	1Mbits	SOP-32pin	25umφ	RJJ03C0130
HN58V1001Txx	HN58V1001RTxx	1Mbits	TSOP-32pin	23umφ	RJJ03C0130
HN58C256AFPxx	HN58C256AFPxx	256Kbits	SOP-28pin	25umφ	RJJ03C0133
HN58C256APxx	HN58C256APxx	256Kbits	DIP-28pin	25umφ	RJJ03C0133
HN58C256ATxx	HN58C256ATxx	256Kbits	TSOP-28pin	23umφ	RJJ03C0133
HN58C257ATxx	HN58C257ATxx	256Kbits	TSOP-32pin	23umφ	RJJ03C0133
HN58V256AFPxx	HN58V256AFPxx	256Kbits	SOP-28pin	25umφ	RJJ03C0132
HN58V256APxx	HN58V256APxx	256Kbits	DIP-28pin	25umφ	RJJ03C0132
HN58V256ATxx	HN58V256ATxx	256Kbits	TSOP-28pin	23umφ	RJJ03C0132
HN58V257ATxx	HN58V257ATxx	256Kbits	TSOP-32pin	23umφ	RJJ03C0132
HN58V65AFPxx	HN58V65AFPxx	64Kbits	SOP-28pin	25umφ	RJJ03C0135
HN58V65APxx	HN58V65APxx	64Kbits	DIP-28pin	25umφ	RJJ03C0135
HN58V65ATxx	HN58V65ATxx	64Kbits	TSOP-28pin	23umφ	RJJ03C0135
HN58V66AFPxx	HN58V66AFPxx	64Kbits	SOP-28pin	25umφ	RJJ03C0135
HN58V66APxx	HN58V66APxx	64Kbits	DIP-28pin	25umφ	RJJ03C0135
HN58V66ATxx	HN58V66ATxx	64Kbits	TSOP-28pin	23umφ	RJJ03C0135